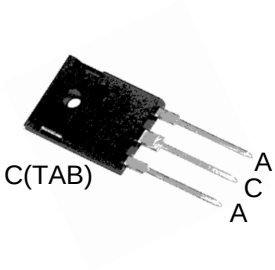
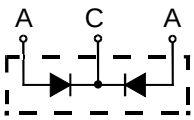
SUR3080PT thru SUR30120PT

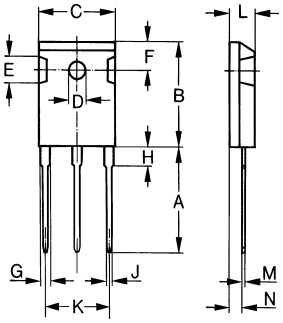
Ultra Fast Recovery Epitaxial Diodes





A=Anode, C=Cathode, TAB=Cathode

Dimensions TO-247AD



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

	V_{RSM} V	V_{RRM} V
SUR3080PT	800	800
SUR30100PT	1000	1000
SUR30120PT	1200	1200

Symbol	Test Conditions		Maximum Ratings	Unit
I_{FRMS} I_{FAVM} I_{FRM}	$T_{VJ}=T_{VJM}$ $T_C=100^oC$; rectangular, d=0.5 t_p<10us; rep. rating, pulse width limited by T_{VJM}		25 15 150	A
I_{FSM}	$T_{VJ}=45^oC$	t=10ms (50Hz), sine t=8.3ms (60Hz), sine	75 80	A
	$T_{VJ}=150^oC$	t=10ms(50Hz), sine t=8.3ms(60Hz), sine	65 70	
I^2t	$T_{VJ}=45^oC$	t=10ms (50Hz), sine t=8.3ms (60Hz), sine	28 27	A^2s
	$T_{VJ}=150^oC$	t=10ms(50Hz), sine t=8.3ms(60Hz), sine	21 20	
T_{VJ} T_{VJM} T_{stg}			-40...+150 150 -40...+150	^oC
P_{tot}	$T_C=25^oC$		78	W
M_d	Mounting torque		0.4...0.6	Nm
Weight			2	g

Sirectifier®

SUR3080PT thru SUR30120PT

Ultra Fast Recovery Epitaxial Diodes

Symbol	Test Conditions	Characteristic Values typ.	max.	Unit
I_R	T_{VJ}=25°C; V_R=V_{RRM} T_{VJ}=25°C; V_R=0.8·V_{RRM} T_{VJ}=125°C; V_R=0.8·V_{RRM}		250 150 4	uA uA mA
V_F	I_F=15A; T_{VJ}=150°C T_{VJ}=25°C		2.2 2.6	V
V_{TO}	For power-loss calculations only		1.65	V
r_T	T_{VJ}=T_{VJM}		46.2	mΩ
R_{thJC} R_{thCK} R_{thJA}		0.5	1.6 60	K/W
t_{rr}	I_F=1A; -di/dt=50A/us; V_R=30V; T_{VJ}=25°C	50	70	ns
I_{RM}	V_R=540V; I_F=15A; -di$_F$/dt=100A/us; L≤0.05uH; T_{VJ}=100°C	6.5	7.2	A

FEATURES

* International standard package JEDEC TO-247AD
* Planar passivated chips
* Very short recovery time
* Extremely low switching losses
* Low I_{RM}-values
* Soft recovery behaviour

APPLICATIONS

* Antiparallel diode for high frequency switching devices
* Antisaturation diode
* Snubber diode
* Free wheeling diode in converters and motor control circuits
* Rectifiers in switch mode power supplies (SMPS)
* Inductive heating and melting
* Uninterruptible power supplies (UPS)
* Ultrasonic cleaners and welders

ADVANTAGES

* High reliability circuit operation
* Low voltage peaks for reduced protection circuits
* Low noise switching
* Low losses
* Operating at lower temperature or space saving by reduced cooling

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SUR3080PT thru SUR30120PT

Ultra Fast Recovery Epitaxial Diodes

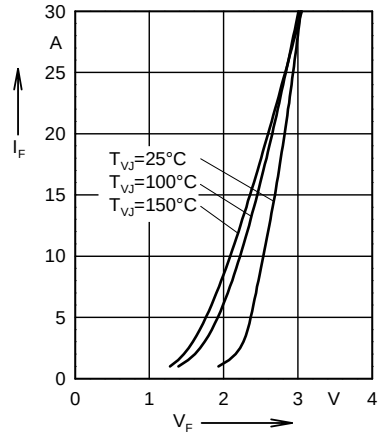


Fig. 1 Forward current versus voltage drop.

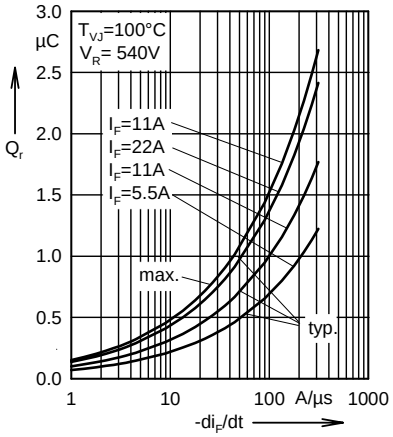


Fig. 2 Recovery charge versus -di$_F$/dt.

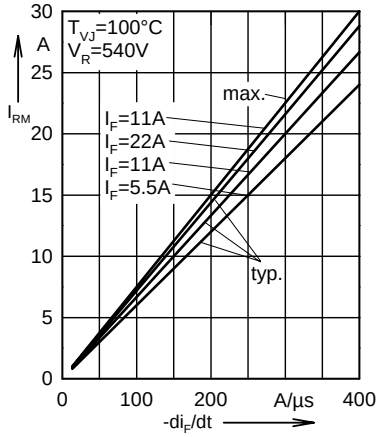


Fig. 3 Peak reverse current versus -di$_F$/dt.

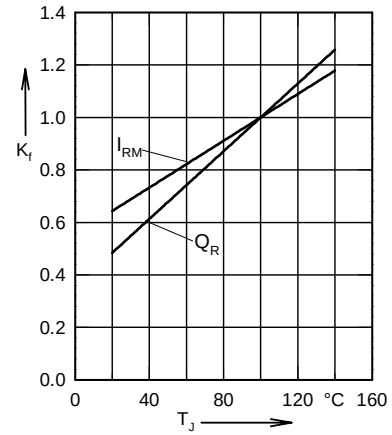


Fig. 4 Dynamic parameters versus junction temperature.

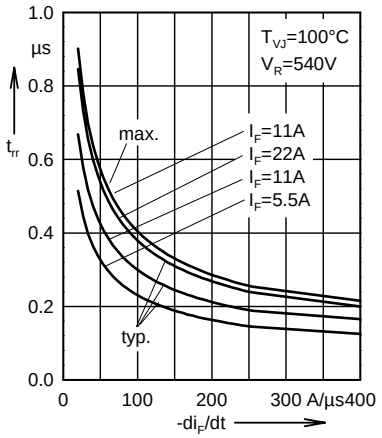


Fig. 5 Recovery time versus -di$_F$/dt.

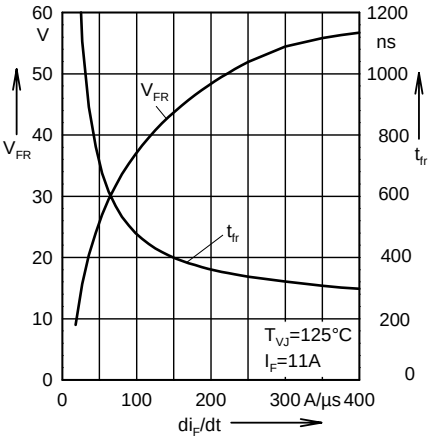


Fig. 6 Peak forward voltage versus di$_F$/dt.

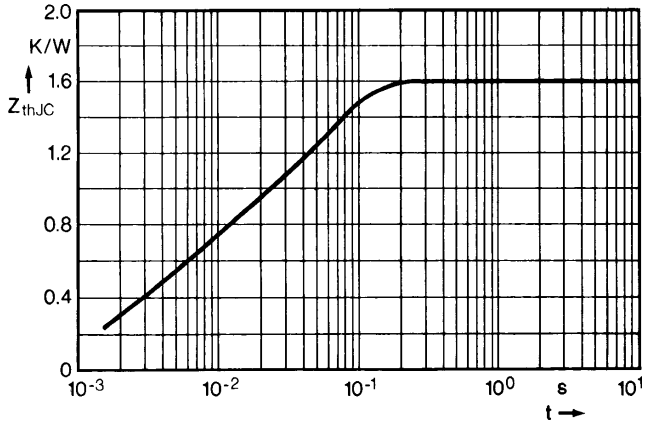


Fig. 7 Transient thermal impedance junction to case.

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